

Landolt-Börnstein Substance/Property Index

III/41: Semiconductors (revised and extended contents of the volumes III/17 and III/22)

Subvolume III/41A2: Impurities and defects in Group IV elements, IV-IV and III-V compounds

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III-V compounds

- | | |
|--|---|
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| aluminum arsenide (AlAs) | indium phosphide (InP) |
| aluminum antimonide (AlSb) | indium arsenide (InAs) |
| gallium nitride (GaN) | indium antimonide (InSb) |

Solid solutions between III-V compounds

- | | |
|--|--|
| GaAs_{1-x} P_x | Ga_{1-x} Al_x Sb |
| GaAs_{1-x} Sb_x | Ga_x In_{1-x} P |
| InAs_{1-x} P_x | Ga_{1-x} In_x As |
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- [Ga_x Al_{1-x} As_y Sb_{1-y}](#)
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Group IV Elements

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